

CP/2814



PATENT APPLICATION

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Hiroyuki ABE et al.

Application No.: 08/930,449

Filed: October 7, 1997

For: HIGH ENERGY SUPPLY APPARATUS, METHOD OF FORMING CRYSTALLINE FILM AND METHOD OF MANUFACTURING THIN FILM ELECTRONIC DEVICE

Group Art Unit: 2814

Examiner: S. Rao

Docket No.: 039514

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AMENDMENT UNDER 37 C.F.R. §1.111

Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

In reply to the September 26, 2002 Office Action, please amend the above-identified application as follows:

IN THE CLAIMS:

Please replace claims 1, 12, 20, 25, 30, 35, 40, 46 and 56 as follows:

The following is a marked-up version of the amended claim(s):

1. (Six Times Amended) A method of forming a crystalline film, comprising:
forming a thin film having a surface on a glass substrate; and
crystallizing at least a surface layer of the thin film by applying energy
through a window that exhibits transparency to the energy to the surface of the thin film,
wherein a distance between the window and the thin film is more than about 20 mm, and at
least the surface layer of the thin film is melted by the applied energy and crystallized by
cooling solidification under a hydrogen-containing atmosphere of at least or approximate
atmospheric pressure,
wherein unpaired bonding electrons on the surface of the thin film during the
cooling solidification are terminated by hydrogen atoms in the hydrogen-containing
atmosphere of at least or approximate atmospheric pressure.